

ABSTRACT OF THE DISCLOSURE

A multi-finger transistor is described, including multiple parallel transistors. Each transistor includes a gate dielectric layer, a gate, a source/drain region, and a drift region in the peripheral substrate of the source/drain region separating the source/drain region and the channel region under the gate. The width of the drift region extending from the side boundary of the source/drain region increases stepwise from the edge sections of the multi-finger transistor toward the central section of the same.